# Low - eld di usion m agneto-therm opower of a high m obility tw o-dim ensional electron 

 gasS. M axim ov, M. G bordzoe, H.Buhm ann and L.W. M olenkam p Physikalisches Institut (EP 3), U niversitat W urzburg, Am H ubland, 97074 W urzburg, Germ any

D. R euter<br>Lehrstuhl fur Festkonperphysik, R uhr-U niversitat B ochum, U niversitatstr. 150, 44801 B ochum , G erm any (D ated: A pril 14, 2024)


#### Abstract

The low magnetic eld diusion therm opower of a high mobility $G$ aA sheterostructure has been $m$ easured directly on an electrostatically de ned $m$ icron-scale $H$ all-bar structure ( 4 m 8 m ) at low temperature ( $T=1: 6 \mathrm{~K}$ ) in the low magnetic eld regime ( $\mathrm{B} \quad 1: 2 \mathrm{~T}$ ) where delocalized quantum $H$ all states do not in uence the $m$ easurem ents. The sam ple design allow ed the determ ination of the eld dependence of the them opower both parallel and perpendicular to the tem perature gradient, denoted respectively by $S_{x x}$ (longitudinal them opower) and $S_{y x}$ (N emstettinghausen coe cient). The experim ental data show clear oscillations in $S_{x x}$ and $S_{y x}$ due to the form ation of Landau levels for 0:3 T $<$ B $1: 2 \mathrm{~T}$ and reveal that $\mathrm{S}_{\mathrm{yx}} \quad 120 \mathrm{~S}_{\mathrm{xx}}$ at a $m$ agnetic eld of 1 T , which agrees well w ith the theoretical prediction that the ratio of these tensor com ponents is dependent on the carrier mobility: $S_{y x}=S_{x x}=2!c$.


K eyw ords: Them oelectric e ect, $m$ agnetotransport
PACS N um bers: 72 20-i, 7220 Pa , 7220 Fr

T herm opow er experim ents have been used extensively to obtain inform ation on transport and scattering in tw odim ensional electron gases ( 2 D EG s) in com pound sem iconductors (for review $S$, see Refs. [1] ] and $[\overline{[1]}]$ ). Because of the strong electron phonon coupling in these system $s$, the experim ental signal is usually dom inated by phonondrag, hence, apart from the desired electronic transport contributions, the signal also contains a very signi cant contribution due to details of the electron-phonon interaction. In order to extract the true electronic or \di usion" therm opower, usually drastic approxim ations have
 have an experim ental approach that is not in uenced by phonon-drage ects and directly yields the di usion therm opower. In this paper we describe the developm ent of such an experim ent.
$W$ e present direct $m$ easurem ents of the $m$ agnetic eld dependence of the di usion therm opower using current heating techniques in specially designed $m$ icro $H$ all bar structures. The sam ples w ere fabricated from high mo bility G aA s-A IG aA s heterostructures [ $100 \mathrm{~m}^{2} /(\mathrm{V} s)$ ] using split-gate techniques. A current passing through an electron channel adjoining the H all structure is used to exclusively heat the electron gas, leaving the lattice tem perature unchanged. This current-heating technique has previously been successfiully used to determ ine the di usion therm opow er of $m$ esoscopic system $s$ such as quan-
 present sam ple design allow s the direct $m$ easurem ent of the tensor com ponents of the them opow er both parallel $\left(S_{x x}\right)$ and perpendicular $\left(S_{y x}\right)$ to the tem perature gradient in $x$-direction. The results are discussed in the fram ew ork of theoreticalm odels developed for the m ag-
netic eld regim e where the form ation of Landau levels leads to a m odulation of the density of states $[\underline{1}, 1]$, but does not yet induce the form ation ofedge states. Therefore, the $m$ agnetic eld in the present study is restricted to the low eld regim e ( $\mathrm{B} \quad 1: 2 \mathrm{~T}$ ) where the in uence of the quantum H alle ect can be neglected.

Fig. 1 show s an SEM -photograph of the sam ple structure, including a schem atic diagram of the $m$ easurem ent. The $m$ icrof H all bar and the electron heating channel are de ned by Schottky-gates, thus form ing the quantum point contacts (QPCs), which are used as voltage probes. G ates A, D, E and F from the $m$ icro $H$ all bar and gates A, B, C and D the heating channel. Utilizing the fact that the them opower of a QPC is quantized [31], QPC 4 and QPC 5 are used to determ ine the electron tem perature in the channel $T_{c h}$ by $m$ easuring the voltage drop $V_{25} \quad V_{5} \quad V_{2}$ across the electron channel, while gates E and F are not de ned. W e then have $\mathrm{V}_{25}=\left(\mathrm{S}_{\text {QPC5 }} \quad \mathrm{S}_{\text {QPC4 }}\right) \mathrm{T}$ ch, where T ch equals the tem perature di erence betw een the electrons in the channel ( $\mathrm{T}_{\mathrm{ch}}$ ) and in the surrounding 2DEG ( $\mathrm{T}_{1}$ 1:6 K), which is in therm alequilibrium $w$ ith the crystal lattice: $\mathrm{T} \mathrm{ch}=\mathrm{T}_{\mathrm{ch}} \quad \mathrm{T}_{1}$ [ $[\mathrm{d}]$. N ote that the tem perature difference $T$ ch enters here rather than a gradient, since the therm ovoltage across a Q PC can only be m easured globally. Experim entally, one observes that $T_{\text {ch }} / I^{2}$, where $I$ is the net heating current, as expected from a sim ple heat balance equation that is valid for not too large current values [ $[\underset{1}{9}] . \mathrm{F}$ ig. 2 show $s$ the experim entally determ ined therm ovoltage as a function of the channel heating current. It can be seen that the parabolic dependence is valid for currents up to 12 A . For the tem perature calibration the therm opow er of Q P C 4 w as adjusted


FIG.1:SEM-photograph of the split-gates structure and the schem e of the $m$ easurem ents.
to $S_{Q P C 4}=20 \mathrm{~V} / \mathrm{K} \overline{\mathrm{p}}$ and the them opower of $\mathrm{QPC} \mathrm{S}_{5}$ $w$ as set at a m inim al value ( $\mathrm{S}_{\mathrm{Q} \text { P c } 5} 0$ ). T he tem perature calibration is given on the right axis of F ig. 2.

For a therm opow er experim ent on the $m$ icro $H$ allbar, Q PC 4 was adjusted into the tunneling regim e $\left(G_{Q P C 4}\right.$
$310^{5} \quad{ }^{1}<e^{2}=h$ ). QPC $1, Q P C_{2}$ and QPC 3 were set to higher conductance values ( $G_{Q P C} \quad 10 \quad 2 e^{2}=h$ ) in order to keep their them opow erm inim al ( $\mathrm{S}_{\mathrm{Q} \text { P C } 1 ; 2 ; 3} 0$ ). $T$ he channel current w as set to 10 A which yields an electron tem perature in the channel of $T_{c h} \quad 6: 6 \mathrm{~K}$ [c.f. Fig. 2]; this current value gave a good com prom ise betw een pronounced therm ovoltage signals and the avoidance of lattice heating e ects. The inset of F ig. 2 show s the longitudinal resistance of the channel at this current level of 10 A; evidently the Shubnikov-de H aas oscillations are nearly suppressed, which ensures an approxim ately constant heat dissipation over the eld range studied.

The experim ents were carried out at a tem perature of about 1.6 K in an ${ }^{4} \mathrm{He}$ cryostat equipped with a 10 T superconducting m agnet. The 2DEG carrier density (2:8 $\quad 10^{15} \mathrm{~m}^{2}$ ) and $\mathrm{mobillty}\left(100 \mathrm{~m}^{2}(\mathrm{~V} \mathrm{~s})^{1}\right)$ were obtained from H all and Shubnikov-de H aas (SdH) $m$ easurem ents. Standard lock-in am pli er m easurem ent techniques were used to $m$ easure the them oelectric effects. A s m entioned above, the 2DEG heating is proportional to $I^{2}$. U sing ac-currents ( $I=i_{0} \cos (!t)$ ) and a lock-in detection of the second harm onic (2!), the $m$ easured signal solely depends on the therm ovoltage $\left.V_{\text {th }} / I^{2}=\left(i_{0} \cos (!t)\right)^{2} / i_{0}^{2} \cos (2!t)\right]$.

Fig. 1 indicates how the tw o tensor com ponents of the


FIG. 2: Electron tem perature as a function of the channel heating current. T he solid line w ith squares represents the $m$ easured data; the dotted line is a parabolic $t$. Inset: Suppression of the SdH oscillations in the channel at a heating current of 10 A. The di erence betw een the dotted line and the $m$ inim um of the SdH is about $15 \%$.
them opow er can be obtained in our current heating experim ent. F irst, we note that the them opower of a 2 DEG in a magnetic eld is a local property, so that the therm ovoltages we $m$ easure are proportional to a tem perature gradient, $V_{\text {th }}=S r_{x} T d x$. $W$ e assume that the tem perature gradient across the m icro H all bar $\mathrm{co}^{-}$ incides w th the line 4-2 connecting QPC 4 and $Q P C_{2}$ de ning the $x$-direction. An im portant param eter for the experim ent is the electron tem perature at the crossing of line 4-2 and the line connecting Q PC $C_{1}$ and QPC (line 1-3 de ning the $y$-direction). If the electron tem perature outside the $m$ icroH all bar is assum ed to be equal to the lattice tem perature, a tem perature gradient is expected to develop between the side which is in contact $w$ ith the heating channel ( $\mathrm{T}_{\mathrm{e}}^{\mathrm{m}} \mathrm{ax} \quad \mathrm{T}_{\mathrm{ch}}$ ) and the surrounding 2DEG $\left(T_{1}\right)$. In zero order approxim ation a constant tem perature gradient along the line connecting $Q P C_{2}$ and $Q P C_{4}$ would have the following form: $r_{x} T_{e}=\left(T_{e}^{m a x} \quad T_{1}\right)=x_{0} \quad 5 \mathrm{~K}=8 \quad \mathrm{~m}=0: 625 \mathrm{~K} / \mathrm{m}$, where $x_{0}$ is the extension of the $m$ icro $H$ all bar in $x-$ direction ( $\mathrm{x}_{0}=8 \mathrm{~m}$ ).

From Fig. 1, it is clear that $V_{Y x}^{\text {th }}$, the them ovoltage perpendicular to the tem perature gradient, can be deter$m$ ined by $m$ easuring the voltage di erence betw een the areas 1 and $3, \mathrm{~V}_{\mathrm{yx}}^{\text {th }} \quad \mathrm{V}_{13} \quad \mathrm{~V}_{3} \quad \mathrm{~V}_{1}$, provided the intrinsic them opow er of QPC 1 and QPC 3 can be neglected. For $\mathrm{V}_{\mathrm{xx}}^{\mathrm{th}}$ how ever, the required voltage probe at the crossing point of the lines 1-3 and 4-2 is not available. Instead, we can obtain $V_{x x}^{\text {th }}$ from $m$ easuring the signals present at $\begin{array}{lllll}V_{12} & V_{2} & V_{1} \text { and } V_{32} & V_{2} & V_{3} \text {. Since } V_{12} \text { and } V_{23}\end{array}$ contain contributions from $\mathrm{V}_{\mathrm{xx}}^{\text {th }}$ as well as $\mathrm{V}_{\mathrm{yx}}^{\text {th }}, \mathrm{V}_{\mathrm{xx}}^{\text {th }}$ can be determ ined by adding $V_{12}$ and $V_{23}$ and subtracting $V_{13} \quad V_{y x}^{\text {th }}$. This allows us to com pare $V_{x x}^{\text {th }}$ and $V_{y x}^{\text {th }}$ directly $w$ ithout an exact know ledge of $r{ }_{x} T_{e}$ in the $m$ icro-


F IG . 3: T hem op ow er $S_{x x}$ parallel to the tem perature gradient: $T$ he solid line corresponds to the experim ental data for $\mathrm{T}=2.5 \mathrm{~K}$ and the dashed dotted line represents the calculation according to Eq. 3.

## Hall structure.

For both com ponents, the experim ents show clear oscillations in the therm opow er w ith $m$ agnetic eld ( $F$ igs. 3 and 4). The them opow er signal has been calculated from the therm ovoltage $m$ easurem ent assum ing the linear tem perature gradient as m entioned above. T he presented eld range studied can be separated into two parts: Finst , $\mathrm{B}<0: 3 \mathrm{~T}$; the electrons are considered as classicalparticles w hich are de ected by the applied magnetic eld and scattered elastically at the device boundaries ( m ean free path $I_{\mathrm{fn}} \mathrm{fp} 8 \mathrm{~m}$ ) [ind, and second, $0: 3<\mathrm{B}<1.2 \mathrm{~T}$ where the oscillations correspond to the form ation ofLandau levels in the 2D EG and hence to the $m$ agnetic eld dependent $m$ odulation of the density of states. In the follow ing, we w ill present a detailed quantitative discussion of the second $m$ agnetic eld regim e ( $0: 3<B<1: 2 \mathrm{~T}$ ) .

A ccording to Ref . [ $\overline{1}_{1}$ ] the $m$ agnetic eld behaviour of the them opow er oscillations can, in the regim e of Landau level form ation, be described by the follow ing equations:

$$
\begin{align*}
& S_{x x}=\frac{2}{1+!_{c}^{2}{ }^{2}} \frac{k_{B}}{e} D^{0}(X) \\
& \exp \frac{2^{2} k_{B} T_{D}}{h!_{c}} \sin \frac{2 f}{B}  \tag{1}\\
& S_{y x}= \\
& \frac{4!_{c}}{1+!_{c}^{2} 2^{2}} \frac{k_{B}}{e} D^{0}(X)  \tag{2}\\
& \exp \quad \frac{2^{2} k_{B} T_{D}}{h!_{c}} \sin \frac{2 f}{B}
\end{align*}
$$

where $T_{D}$ is the $D$ ingle tem perature, $!_{c}$ the cyclotron frequency, the transport relaxation tim e, and $f$ is the frequency of the oscillations $\left(f=B=E_{F}=h!_{c}\right.$, where $E_{F}$


FIG.4: Therm opower $S_{y x}$ perpendicular to the tem perature gradient: $T$ he solid line corresponds to the experim ental data for $T=2.5 \mathrm{~K}$ and the dashed dotted line represents the calculation according to Eq. 4.
is the Fem ienergy). T he quantity $\mathrm{D}^{0}(\mathrm{X})$ is the derivative of the them al dam ping factor $D(X)$, de ned by $D(X)=X=\sinh X$ where $X=2^{2} k_{B} T=h!{ }_{c}$. These equations w ere originally [7] derived for conditions w here $!_{\mathrm{c}}<1$, which would restrict the validity in our case to m agnetic elds up to B $20 \mathrm{~m} \mathrm{~T} . \mathrm{H}$ ow ever, C oleridge et al. [12] have show $n$ that Eqs. (3) and (4) are valid up to much higher eld vahes (B 1 T) when localization e ects can be neglected (as it is the case for high mobility 2D EGS).

T he results of the m easurem ents up to 12 T are presented in Fig. 3 and $F i g .4$ together with ts using Eqns. ( $\overline{1}_{1}^{1}$ ) and (2). For the $t s$, the carrier density $n$ and the mobility were taken from the transport characterization. T he D ingle tem perature w as obtained from the assum ption that the quantum $m$ obility is approxim ately 10 tim es lower than the electron mobility i.e. $\mathrm{T}_{\mathrm{D}} \quad 10=0: 4 \mathrm{~K}$ [hin 10 T . T he them al sm earing w as tted by a free param eter $\mathrm{T}_{\mathrm{e}}$, which can be intenpreted as the average electron tem perature in the m icro H all bar. $T$ he best ts for an average electron tem perature of $\overline{\mathrm{T}}_{\mathrm{e}}=4 \mathrm{~K}$ is in very good agreem ent w ith the estim ates m ade above conceming the tem perature gradient.

B oth $S_{x x}$ and $S_{y x}$ can be tted satisfactorily using the sam e set of param eters, even though the am plitudes are very di erent. A coording to Eqns. (3) and (4), the ratio of the them opow er perpendicular and parallel to the tem perature gradient is given by $S_{y x}=S_{x x}=2!_{c}$. For the present sample, the $m$ easured ratio at $B=1$ $T$ is 120. Again, this value agrees well w ith the expected value of 160. To our know ledge this is the rst successfill m easurem ent of the di usion them opower for a sem iconductor 2D EG system. T he current heating approach allow sus to avoid the in uence ofphonon-drag e ects
tem peratures and the tem perature gradients, which are obtained from the tting and the channel tem perature calibration, it can be concluded that the chosen geom etry and the $m$ easurem ent con guration are suitable for investigating the di usion therm opow er of high $m$ obility sam ples.

Sum m arizing, the results presented here dem onstrate that electron heating techniques can be used to $m$ easure directly the longitudinal and transverse com ponents of the di usion them opower. For low m agnetic elds, ther$m$ opower uctuations are observed which originate from quasi-ballistic electrons; for higher elds, the m odulation of the electron density of states due to Landau level form ation determ ines the oscillatory part of the di usion them opower. C urrent theories $\left[\begin{array}{lll}{[1,} & 1 \\ \hline\end{array}\right.$ oscillatory behavior to a large extent and can be used to independently gauge the electron tem perature. The consistency of these $m$ easurem ents $w$ ith theory opens up the $w$ ay for an altemative $m$ ethod for studying the di $u$ sion therm opower in the QHE as wellas in the fractional quantum $H$ alle ect regim $e$, where currently, experim en-

$T$ his work perform ed w ith nancial support from the D eutsche Forschungsgem einschaft (DFG M $\circ 771 / 5-2$ ).
[1] R . F letcher, Sem icond. Sci. Technol. Vol14, R 1 (1999).
[2] B L. G allagher and P N. Butcher, in H andbook on Sem iconductors, edited by P.T. Landsberg, (E lsevier, Am sterdam ), Vol. 1, p. 817 (1992).
[3] L W . . M olenkam P, H . van H outen, C W J. B eenakker, R . Eppenga, C.T.Foxon, P hys. R ev. Lett., 651052 (1990).
[4] A A M . Staring, L W . M olenkam p, B W . A lphenaar, H . van H outen, O JA. Buyk, M A A. M abesoone, C .W J. Beenakker, and C.T. Foxon, Europhys. Lett. 22, 57 (1993).
[5] S. M oller, H . Buhm ann, SF. Godijn, and L W . M olenkam p, P hys. R ev. Lett., 81, 5197 (1998).
[6] S F. G odijn, S . M oller, H . B uhm ann, L .W . M olenkam p, and S A. van Langen, P hys. Rev. Lett., 82, 2927 (1999).
[7] R . F letcher, P.T. C oleridge and Y.Feng, P hys. Rev. B , 522823 (1995).
[8] L.W . M olenkam P, H . van H outen, C W . B eenakker, R . Eppenga and C.T.Foxon, C ondensed System sofLow D i$m$ ensionality, edited by J.L. B eeby et al., P lenum P ress, N ew York, p. 335 (1991).
[9] H . van H outen, L .W . M olenkam p, C .W J. B eenakker, and C.T.Foxon, Sem icond. Sci. Technol7, B 215 (1992).
[10] For a qualitative and quantitative discussion of the low m agnetic eld regim e ( $0 \quad \mathrm{~B}<0: 3 \mathrm{~T}$ ) a detailed theoreticalm odelling of the ballistic therm opow er of th is special sam ple geom etry is needed including a num erical calculation of the related transm ission probabilities [11], which will be given in a later publication.
[11] A.G. P ogosov, M .V.Budantsev, D . U zur, A. N ogaret, A E. P lotnikov, A K . B akarov, and A .I. T oropov, P hys. Rev.B 66, 201303R (2002).
[12] P .T . C oleridge, R . Stoner, R . F letcher, P hys. R ev . B , 39 1120 (1989).
[13] G F. G iuliani and JJ. Q uinn, Phys. Rev. B 264421 (1982).
[14] R . F letcher, V M .P udalov, Y .Feng, M .T saousidou, P N . B utcher, P hys. Rev.B, 56, 12422, (1997).
[15] R.F letcher, V M P udalov and S.C ao, P hys. R ev. B 57, 7174, (1998).
[16] B. T ieke, R . F letcher, U . Zeitler, M . H enini and J.C . M aan, Phys. Rev.B 58, 2017 (1999).
[17] X . Y ing, V . B ayot, M B. Santos and M . Shayegan, P hys. Rev.B 50, 4969, (1994).
[18] D .V . K hveshchenko, P hys. Rev. B , 54, R 14317, (1996).

